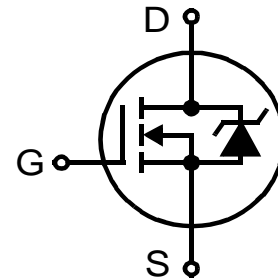


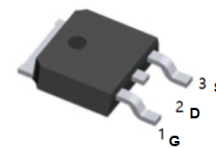
Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(ON)}$ and fast switching speed.



Features

- V_{DS} (V) = 30V
- I_D = 35A (V_{GS} = 10V)
- $R_{DS(ON)}$ = 5.7m Ω (V_{GS} = 10V)
- $R_{DS(ON)}$ = 6.8m Ω (V_{GS} = 4.5V)



TO-252(DPAK) top view

MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|---|------------|---------------------|
| V_{DSS} | Drain to Source Voltage | 30 | V |
| V_{GS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current | | |
| | Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$) (Note 1) | 94 | A |
| | Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 4.5\text{V}$) (Note 1) | 85 | A |
| | Continuous ($T_{amb} = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, with $R_{\theta JA} = 52^\circ\text{C/W}$) | 17 | A |
| | Pulsed | Figure 4 | A |
| E_{AS} | Single Pulse Avalanche Energy (Note 2) | 168 | mJ |
| P_D | Power dissipation | 80 | W |
| | Derate above 25°C | 0.53 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Temperature | -55 to 175 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case TO-252 | 1.88 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient TO-252 | 100 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient TO-252, 1in ² copper pad area | 52 | $^\circ\text{C/W}$ |

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|------------|-----------------------------------|--|----|---|-----------|---------------|
| B_{VDSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 30 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24\text{V}$ $V_{GS} = 0\text{V}$ $T_C = 150^\circ\text{C}$ | - | - | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|----------------------------------|---|-----|----|-----|------------|
| $V_{GS(TH)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ | 1.2 | - | 2.5 | V |
| $r_{DS(ON)}$ | Drain to Source On Resistance | $I_D = 35\text{A}, V_{GS} = 10\text{V}$ | - | 47 | 57 | m Ω |
| | | $I_D = 35\text{A}, V_{GS} = 4.5\text{V}$ | - | 57 | 68 | |
| | | $I_D = 35\text{A}, V_{GS} = 10\text{V},$ $T_J = 175^\circ\text{C}$ | - | 75 | 92 | |

Dynamic Characteristics

| | | | | | | | |
|--------------|----------------------------------|---|---|------|-----|----------|----|
| C_{ISS} | Input Capacitance | $V_{DS} = 15\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$ | - | 2525 | - | pF | |
| C_{OSS} | Output Capacitance | | - | 490 | - | pF | |
| C_{RSS} | Reverse Transfer Capacitance | | - | 300 | - | pF | |
| R_G | Gate Resistance | $V_{GS} = 0.5\text{V}, f = 1\text{MHz}$ | - | 2.1 | - | Ω | |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V | $V_{GS} = 0\text{V to } 10\text{V}$ | $V_{DD} = 15\text{V}$ $I_D = 35\text{A}$ $I_g = 1.0\text{mA}$ | - | 46 | 60 | nC |
| $Q_{g(5)}$ | Total Gate Charge at 5V | $V_{GS} = 0\text{V to } 5\text{V}$ | | - | 24 | 32 | nC |
| $Q_{g(TH)}$ | Threshold Gate Charge | $V_{GS} = 0\text{V to } 1\text{V}$ | | - | 2.3 | 3.0 | nC |
| Q_{gs} | Gate to Source Gate Charge | | | - | 6.9 | - | nC |
| Q_{gs2} | Gate Charge Threshold to Plateau | | | - | 4.6 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | - | 9.8 | - | nC |

Switching Characteristics ($V_{GS} = 10\text{V}$)

| | | | | | | |
|--------------|---------------------|--|---|-----|-----|----|
| t_{ON} | Turn-On Time | $V_{DD} = 15\text{V}, I_D = 35\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 6.2\Omega$ | - | - | 171 | ns |
| $t_{d(ON)}$ | Turn-On Delay Time | | - | 9 | - | ns |
| t_r | Rise Time | | - | 106 | - | ns |
| $t_{d(OFF)}$ | Turn-Off Delay Time | | - | 53 | - | ns |
| t_f | Fall Time | | - | 41 | - | ns |
| t_{OFF} | Turn-Off Time | | - | - | 143 | ns |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|-------------------------------|---|---|---|------|----|
| V_{SD} | Source to Drain Diode Voltage | $I_{SD} = 35\text{A}$ | - | - | 1.25 | V |
| | | $I_{SD} = 15\text{A}$ | - | - | 1.0 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 35\text{A}, dl_{SP}/dt = 100\text{A}/\mu\text{s}$ | - | - | 27 | ns |
| Q_{RR} | Reverse Recovered Charge | $I_{SD} = 35\text{A}, dl_{SP}/dt = 100\text{A}/\mu\text{s}$ | - | - | 12 | nC |

Notes:

1: Package current limitation is 35A.

 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.43\text{mH}$, $I_{AS} = 28\text{A}$, $V_{DD} = 27\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

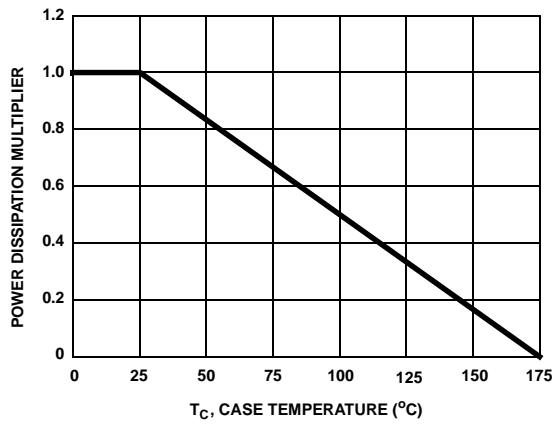


Figure 1. Normalized Power Dissipation vs Case Temperature

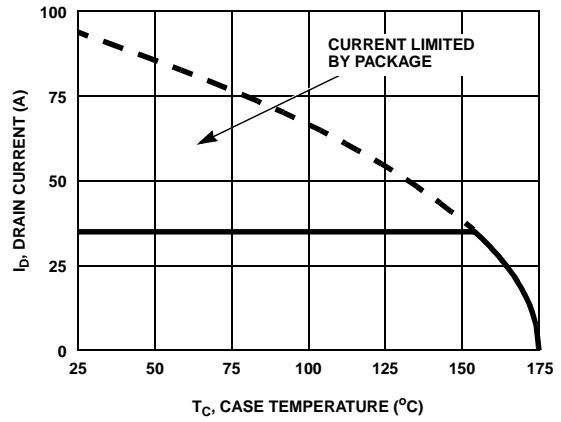


Figure 2. Maximum Continuous Drain Current vs Case Temperature

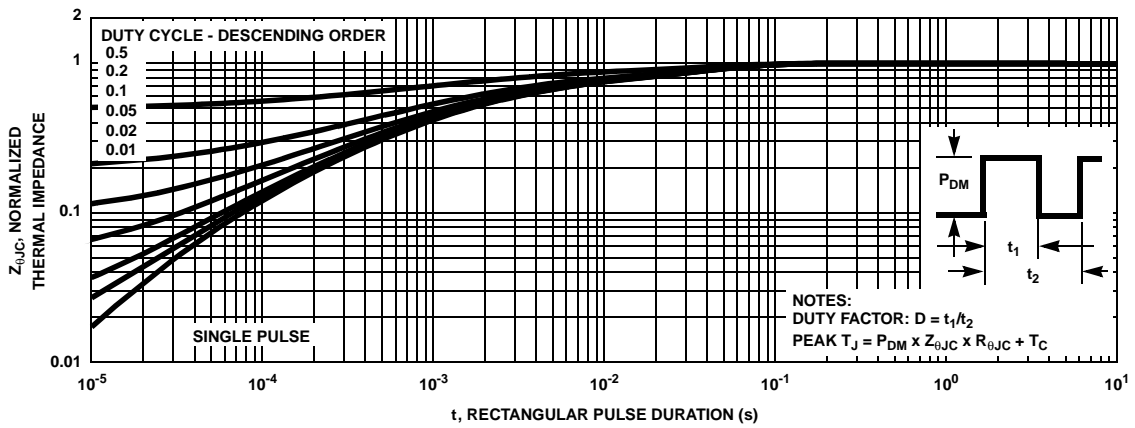


Figure 3. Normalized Maximum Transient Thermal Impedance

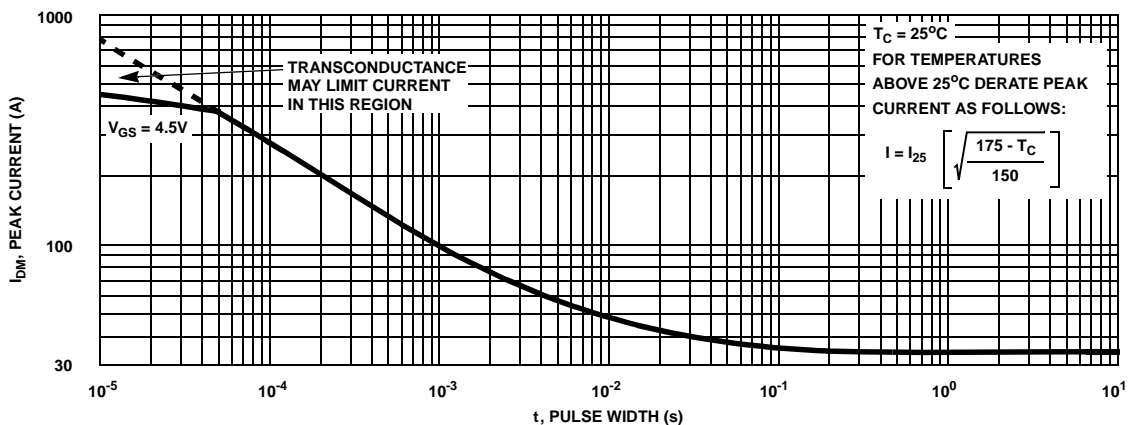


Figure 4. Peak Current Capability

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

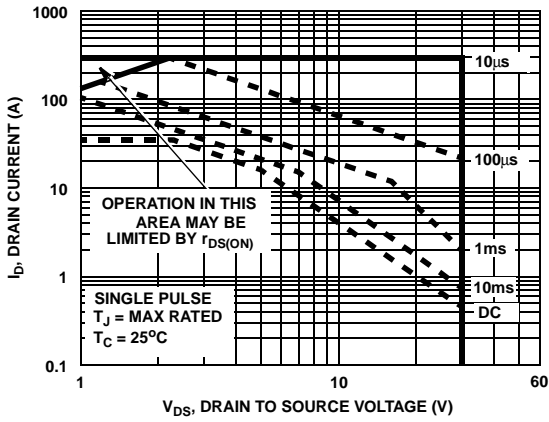
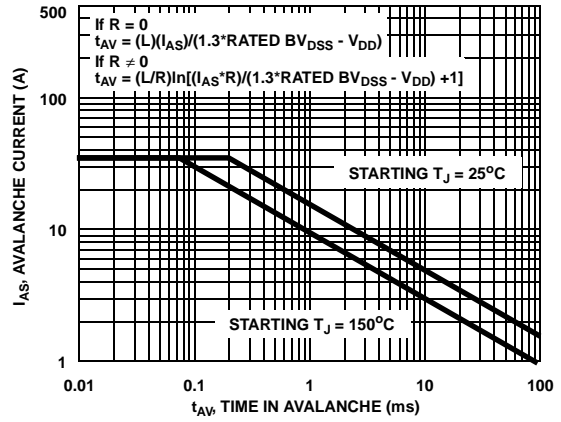


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

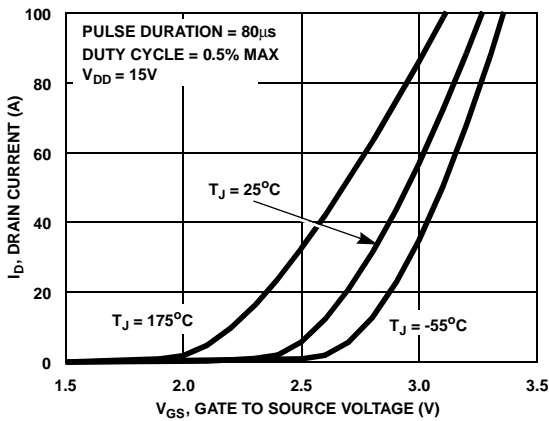


Figure 7. Transfer Characteristics

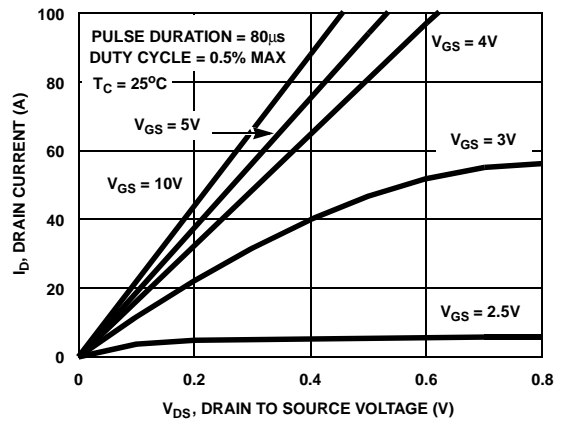


Figure 8. Saturation Characteristics

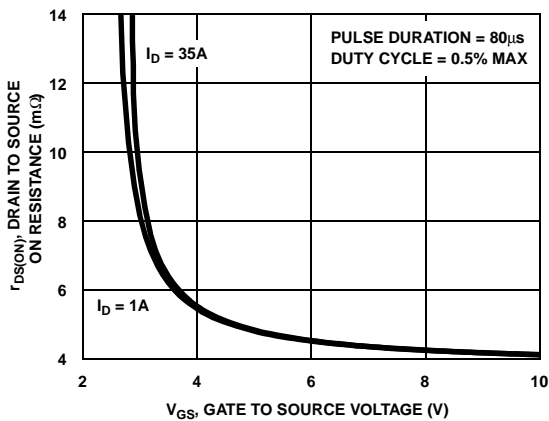


Figure 9. Drain to Source On Resistance vs Gate Voltage and Drain Current

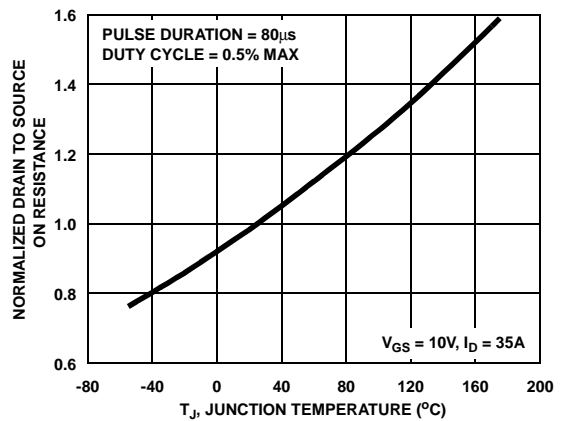


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

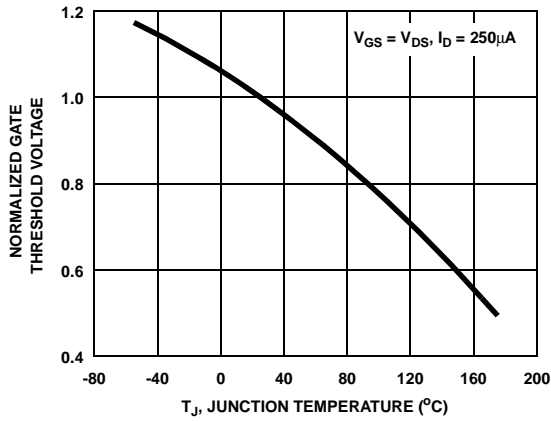


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

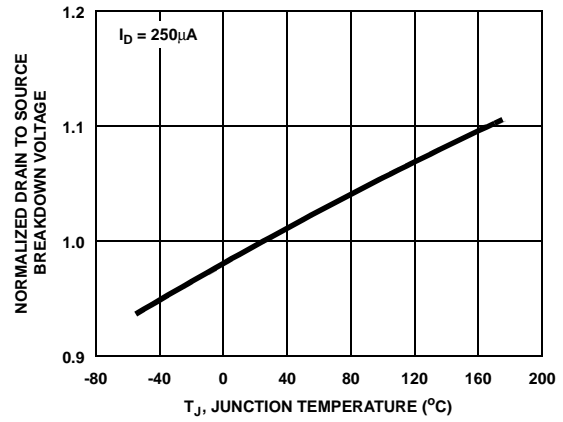


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

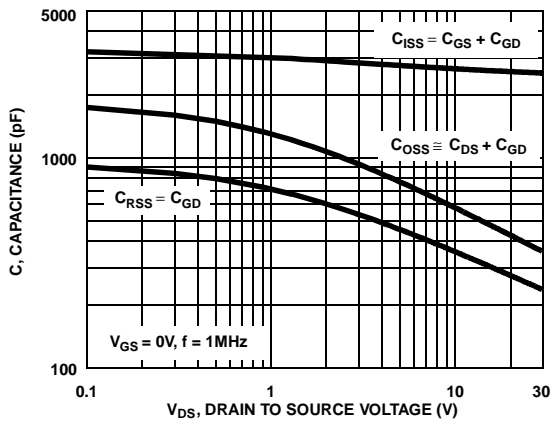


Figure 13. Capacitance vs Drain to Source Voltage

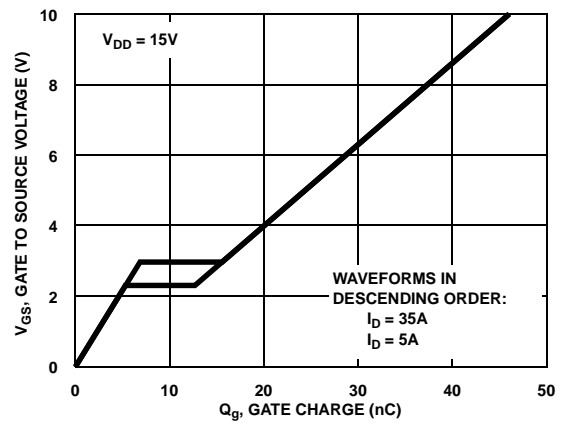


Figure 14. Gate Charge Waveforms for Constant Gate Current

Test Circuits and Waveforms

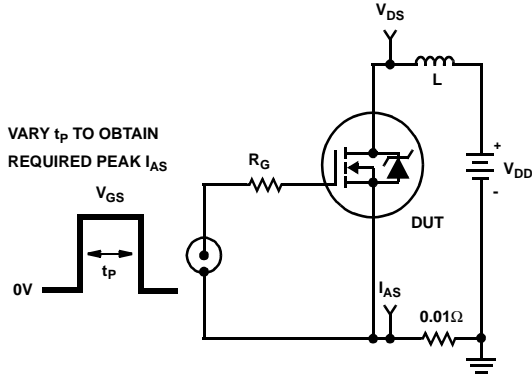


Figure 15. Unclamped Energy Test Circuit

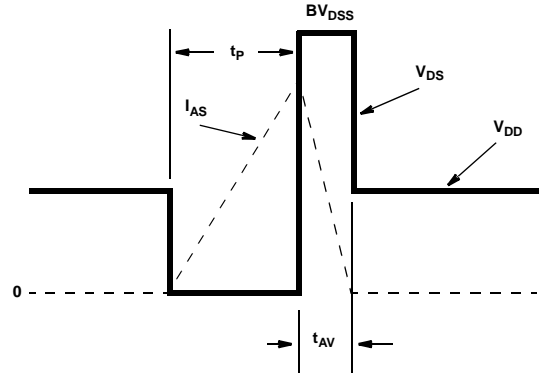


Figure 16. Unclamped Energy Waveforms

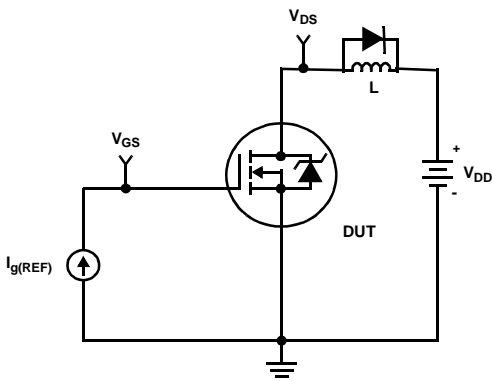


Figure 17. Gate Charge Test Circuit

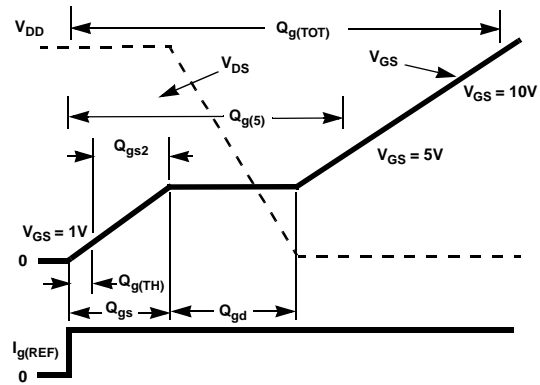


Figure 18. Gate Charge Waveforms

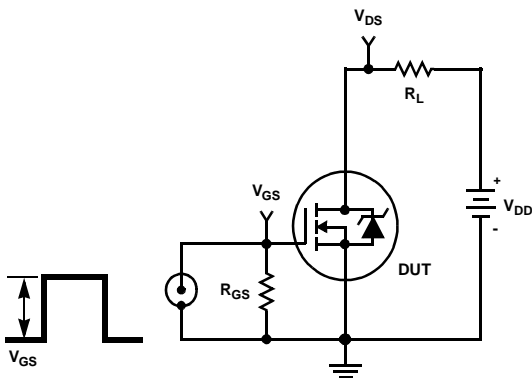


Figure 19. Switching Time Test Circuit

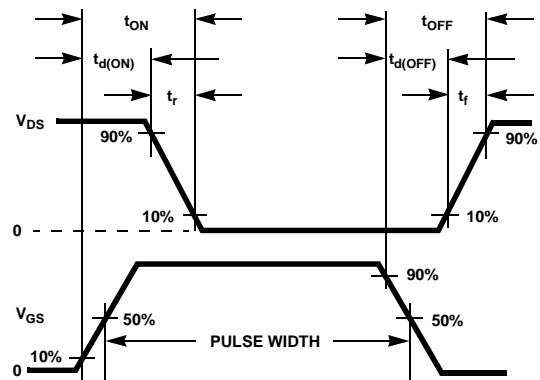
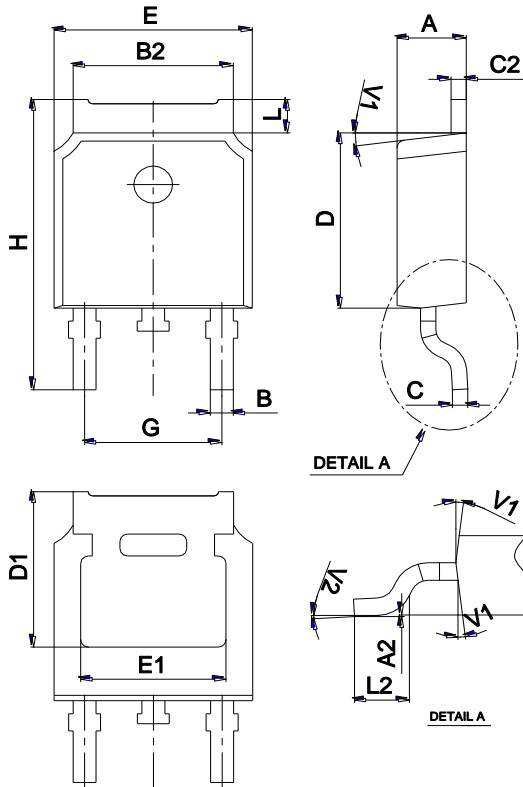


Figure 20. Switching Time Waveforms

Package Mechanical Data TO-252



| Ref. | Dimensions | | | | | |
|------|-------------|------|-------|----------|------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.10 | | 2.50 | 0.083 | | 0.098 |
| A2 | 0 | | 0.10 | 0 | | 0.004 |
| B | 0.66 | | 0.86 | 0.026 | | 0.034 |
| B2 | 5.18 | | 5.48 | 0.202 | | 0.216 |
| C | 0.40 | | 0.60 | 0.016 | | 0.024 |
| C2 | 0.44 | | 0.58 | 0.017 | | 0.023 |
| D | 5.90 | | 6.30 | 0.232 | | 0.248 |
| D1 | 5.30REF | | | 0.209REF | | |
| E | 6.40 | | 6.80 | 0.252 | | 0.268 |
| E1 | 4.63 | | | 0.182 | | |
| G | 4.47 | | 4.67 | 0.176 | | 0.184 |
| H | 9.50 | | 10.70 | 0.374 | | 0.421 |
| L | 1.09 | | 1.21 | 0.043 | | 0.048 |
| L2 | 1.35 | | 1.65 | 0.053 | | 0.065 |
| V1 | | 7° | | | 7° | |
| V2 | 0° | | 6° | 0° | | 6° |

Ordering information

| Order code | Package | Baseqty | Delivery mode |
|-------------|---------|---------|---------------|
| UMW FDD8896 | TO-252 | 2500 | Tape and reel |